

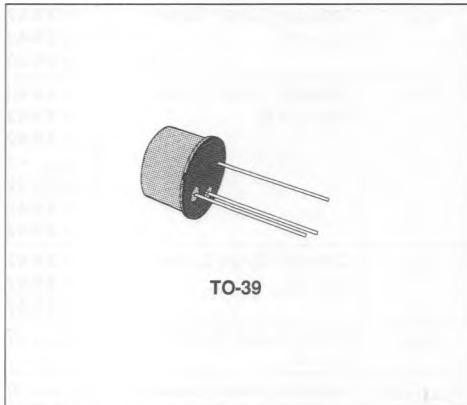
## MEDIUM POWER GENERAL PURPOSE TRANSISTORS

### DESCRIPTION

The 2N4234, 2N4235 and 2N4236 are silicon epitaxial planar PNP transistors mounted in Jedec TO-39 metal case.

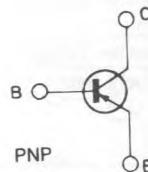
They are intended for use in switching and amplifier applications.

The complementary NPN types are the 2N4237, and 2N4238 and 2N4239 respectively.



TO-39

### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	2N4234	2N4235	2N4236	Unit
$V_{CBO}$	Collector-base Voltage ( $I_E = 0$ )	- 40	- 60	- 80	V
$V_{CEO}$	Collector-emitter Voltage ( $I_B = 0$ )	- 40	- 60	- 80	V
$V_{EBO}$	Emitter-base Voltage ( $I_C = 0$ )		- 7		V
$I_C$	Collector Current		- 3		A
$I_B$	Base Current		- 0.2		A
$P_{tot}$	Total Power Dissipation at $T_{case} \leq 25^\circ\text{C}$ $T_{amb} \leq 25^\circ\text{C}$	6	1		W W
$T_{stg}$	Storage Temperature	- 65 to 200			°C
$T_J$	Junction Temperature	200			°C

## THERMAL DATA

$R_{th\ j\ -case}$	Thermal Resistance Junction-case	Max	29	$^{\circ}C/W$
$R_{th\ j\ -amb}$	Thermal Resistance Junction-ambient	Max	175	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^{\circ}C$  unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CBO}$	Collector Cutoff Current ( $I_E = 0$ )	for 2N4234 $V_{CE} = - 40V$ for 2N4235 $V_{CE} = - 60V$ for 2N4236 $V_{CE} = - 80V$			- 0.1	mA
$I_{CEV}$	Collector Cutoff Current ( $V_{BE} = 1.5$ )	for 2N4234 $V_{CE} = - 40V$ for 2N4235 $V_{CE} = - 60V$ for 2N4236 $V_{CE} = - 80V$ $T_{case} = 150^{\circ}C$ for 2N4234 $V_{CE} = - 30V$ for 2N4235 $V_{CE} = - 40V$ for 2N4236 $V_{CE} = - 60V$			- 0.1 - 0.1 - 0.1 - 1 - 1 - 1	mA mA mA mA mA mA
$I_{CEO}$	Collector Cutoff Current ( $I_B = 0$ )	for 2N4234 $V_{CE} = - 30V$ for 2N4235 $V_{CE} = - 40V$ for 2N4236 $V_{CE} = - 60V$			- 1 - 1 - 1	mA mA mA
$I_{EBO}$	Emitter Cutoff Current ( $I_C = 0$ )	$V_{EB} = 7V$			- 0.5	mA
$V_{CEO(sus)}^*$	Collector-emitter Sustaining Voltage ( $I_B = 0$ )	$I_C = - 100mA$ for 2N4234 for 2N4235 for 2N4236	- 40 - 60 - 80			V V V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = - 1A$ $I_B = - 100mA$			- 0.6	V
$V_{BE(sat)}^*$	Base-emitter Saturation Voltage	$I_C = - 1A$ $I_B = - 100mA$			- 1.5	V
$V_{BE}^*$	Base-emitter Voltage	$I_C = - 0.25A$ $V_{CE} = - 1V$			- 1	V
$h_{FE}^*$	DC Current Gain	$I_C = - 100mA$ $V_{CE} = - 1V$ $I_C = - 250mA$ $V_{CE} = - 1V$ $I_C = - 500mA$ $V_{CE} = - 1V$ $I_C = - 1A$ $V_{CE} = - 1V$	40 30 20 10		150	
$f_T$	Transition Frequency	$I_C = - 100mA$ $V_{CE} = - 10V$ $f = 1MHz$	3			MHz
$C_{CBO}$	Collector-base Capacitance	$I_E = 0$ $V_{CB} = - 10V$ $f = 100KHz$			100	pF
$h_{fe}$	Small Signal Current Gain	$I_C = - 50mA$ $V_{CE} = - 10V$ $f = 1KHz$	25			

\* Pulsed : pulse duration = 300μs, duty cycle ≤ 2%.